Low-power dual unbuffered inverter

Rev. 4 — 7 December 2011

**Product data sheet** 

### 1. General description

The 74AUP2GU04 provides two unbuffered inverting gates.

This device ensures a very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V.

### 2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; I<sub>CC</sub> = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

### 3. Ordering information

Table 1. Ordering information											
Type number	Type number Package										
	Temperature range	Name	Description	Version							
74AUP2GU04GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363							
74AUP2GU04GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1.45 $\times$ 0.5 mm	SOT886							
74AUP2GU04GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 $\times$ 1 $\times$ 0.5 mm	SOT891							
74AUP2GU04GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115							
74AUP2GU04GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202							



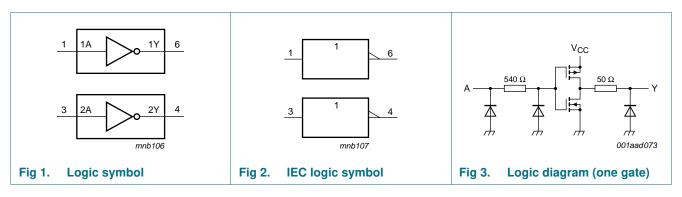
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### 4. Marking

Table 2.   Marking	
Type number	Marking code <sup>[1]</sup>
74AUP2GU04GW	aD
74AUP2GU04GM	aD
74AUP2GU04GF	aD
74AUP2GU04GN	aD
74AUP2GU04GS	aD

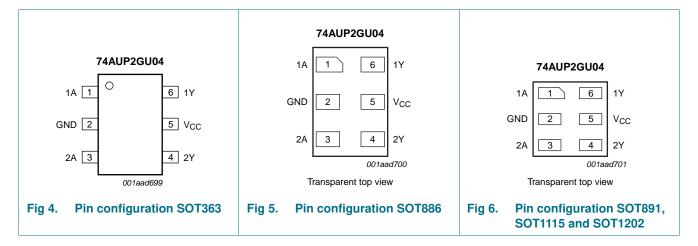
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 5. Functional diagram



## 6. **Pinning information**

### 6.1 Pinning



### 6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
$V_{CC}$	5	supply voltage
1Y	6	data output

### 7. Functional description

#### Table 4. Function table<sup>[1]</sup>

Input	Output
nA	nY
L	Н
Н	L

[1] H = HIGH voltage level;

L = LOW voltage level.

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage		[2] _0.5	$V_{CC} + 0.5$	V
lo	output current	$V_{O} = 0 V$ to $V_{CC}$	-	±20	mA
I <sub>CC</sub>	supply current		-	50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	<u>[3]</u> _	250	mW

[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

[2] The output voltage ratings may be exceeded if the output current ratings are observed.

[3] For SC-88 packages: above 87.5 °C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

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## 9. Recommended operating conditions

Table 6.	Recommended operating condition	ons			
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage		0	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	0	200	ns/V
					-

## **10. Static characteristics**

#### Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
T <sub>amb</sub> = 2	5 °C					
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 0.8 V$ to 3.6 V	$0.75 \times V_{CC}$	-	-	۷
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$ to 3.6 V	-	-	$0.25 \times V_{CC}$	۷
V <sub>OH</sub>	HIGH-level output voltage	$V_I = GND \text{ or } V_{CC}$				
		$I_O$ = –20 $\mu A;V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	۷
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	٧
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	۷
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	٧
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = GND \text{ or } V_{CC}$				
		$I_O$ = 20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3 \times V_{CC}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l <sub>l</sub>	input leakage current	$V_1 = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μA
I <sub>CC</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ \text{A}; \\ V_{CC} = 0.8 \ \text{V} \text{ to } 3.6 \ \text{V} \end{array}$	-	-	0.5	μA
Cı	input capacitance	$V_{CC}$ = 0 V to 3.6 V; $V_I$ = GND or $V_{CC}$	-	1.5	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.8	-	pF
	· · ·		-		-	

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Symbol	Parameter	Conditions	Min	Тур	Max	Uni
T <sub>amb</sub> = –	40 °C to +85 °C					
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 0.8 V$ to 3.6 V	$0.75 \times V_{CC}$	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 V$ to 3.6 V	-	-	$0.25\times V_{CC}$	V
V <sub>OH</sub>	HIGH-level output voltage	$V_I = GND \text{ or } V_{CC}$				
		$I_O = -20~\mu A;~V_{CC} = 0.8~V$ to 3.6 $V$	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	۷
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = GND \text{ or } V_{CC}$				
		$I_O$ = 20 $\mu A;V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	٧
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	$0.3\times V_{CC}$	۷
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	٧
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μA
lcc	supply current	$\label{eq:VI} \begin{array}{l} V_{I}=GND \text{ or } V_{CC}; \ I_{O}=0 \ \text{A}; \\ V_{CC}=0.8 \ \text{V to } 3.6 \ \text{V} \end{array}$	-	-	0.9	μA
Γ <sub>amb</sub> = –	40 °C to +125 °C					
/ <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 0.8 V$ to 3.6 V	$0.75 \times V_{CC}$	-	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC} = 0.8 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	$0.25 \times V_{CC}$	V
√ <sub>ОН</sub>	HIGH-level output voltage	$V_I = GND \text{ or } V_{CC}$				
		$I_O$ = –20 $\mu A;  V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.11$	-	-	٧
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V

#### Table 7. Static characteristics ...continued

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#### Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>OL</sub>	LOW-level output voltage	$V_I = GND \text{ or } V_{CC}$				
		$I_O$ = 20 $\mu A;V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.33 \times V_{CC}$	V
		$I_{O}$ = 1.7 mA; $V_{CC}$ = 1.4 V	-	-	0.41	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.39	V
		$I_{O}$ = 2.3 mA; $V_{CC}$ = 2.3 V	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O}$ = 2.7 mA; $V_{CC}$ = 3.0 V	-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
l <sub>l</sub>	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.75	μA
I <sub>CC</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = O \ A; \\ V_{CC} = 0.8 \ V \ to \ 3.6 \ V \end{array}$	-	-	1.4	μA

## **11. Dynamic characteristics**

#### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions			25 °C		-40	°C to +1	25 °C	Unit
				Min	Typ[1]	Мах	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 5 p	F									
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	6.2	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		0.9	2.3	4.4	0.9	4.8	5.3	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V		0.7	1.7	3.1	0.6	3.4	3.8	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		0.5	1.4	2.6	0.5	2.9	3.2	ns
		$V_{CC}$ = 2.3 V to 2.7 V		0.4	1.1	2.0	0.4	2.3	2.6	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		0.3	1.0	1.8	0.3	2.1	2.4	ns
C <sub>L</sub> = 10	pF									
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	9.6	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		1.2	3.1	6.1	1.2	6.8	7.5	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V		1.0	2.3	4.0	0.9	4.6	5.1	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		0.8	1.9	3.3	0.7	3.8	4.2	ns
		$V_{CC}$ = 2.3 V to 2.7 V		0.6	1.5	2.7	0.6	3.1	3.5	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		0.5	1.3	2.4	0.5	2.7	3.0	ns

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Symbol	Parameter	Conditions	Conditions		25 °C		–40 °C to +125 °C			Unit
			-	Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C <sub>L</sub> = 15	pF		I					1		
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	13.0	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		1.6	3.8	7.9	1.4	8.8	9.7	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		1.3	2.8	4.9	1.1	5.7	6.3	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		1.0	2.3	4.0	0.9	4.7	5.2	ns
		$V_{CC}$ = 2.3 V to 2.7 V		0.8	1.9	3.2	0.8	3.7	4.1	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		0.7	1.6	2.9	0.7	3.3	3.7	ns
C <sub>L</sub> = 30	pF									
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	23.2	-	-	-	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		2.4	6.0	13.1	2.2	14.8	16.3	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.0	4.2	7.6	1.8	9.0	9.9	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		1.7	3.6	6.1	1.5	7.2	8.0	ns
		$V_{CC}$ = 2.3 V to 2.7 V		1.4	2.9	4.8	1.3	5.7	6.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		1.2	2.5	4.3	1.1	5.1	5.7	ns
C <sub>L</sub> = 5 p	F, 10 pF, 15 pF and	30 pF								
C <sub>PD</sub>	power dissipation	$f_i = 1 \text{ MHz}; V_I = GND \text{ to } V_{CC}$	[3][4]							
	capacitance	$V_{CC} = 0.8 V$		-	1.1	-	-	-	-	pF
		V <sub>CC</sub> = 1.1 V to 1.3 V		-	1.1	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		-	1.3	-	-	-	-	pF
		V <sub>CC</sub> = 1.65 V to 1.95 V		-	1.5	-	-	-	-	pF
		$V_{CC}$ = 2.3 V to 2.7 V		-	3.0	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		-	4.5	-	-	-	-	pF

#### Table 8. Dynamic characteristics ... continued

[1] All typical values are measured at nominal V<sub>CC</sub>.

[2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[3] All specified values are the average typical values over all stated loads.

[4]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_{D} = C_{PD} \times V_{CC}{}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}{}^{2} \times f_{o}) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

 $C_L$  = load capacitance in pF;

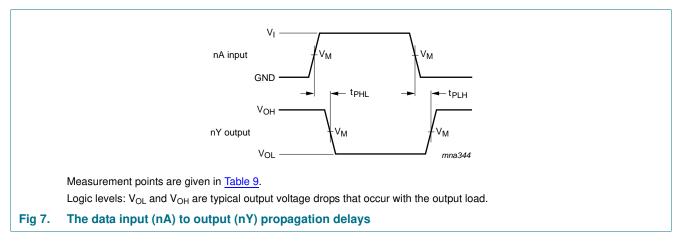
V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

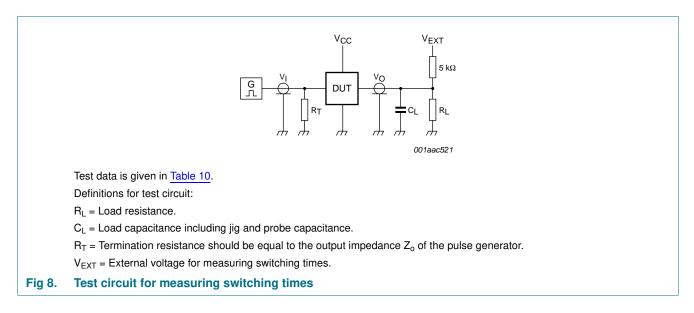
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## 12. Waveforms



#### Table 9.Measurement points

Supply voltage	Output	Input				
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	VI	t <sub>r</sub> = t <sub>f</sub>		
0.8 V to 3.6 V	$0.5  imes V_{CC}$	$0.5  imes V_{CC}$	V <sub>CC</sub>	$\leq$ 3.0 ns		



#### Table 10. Test data

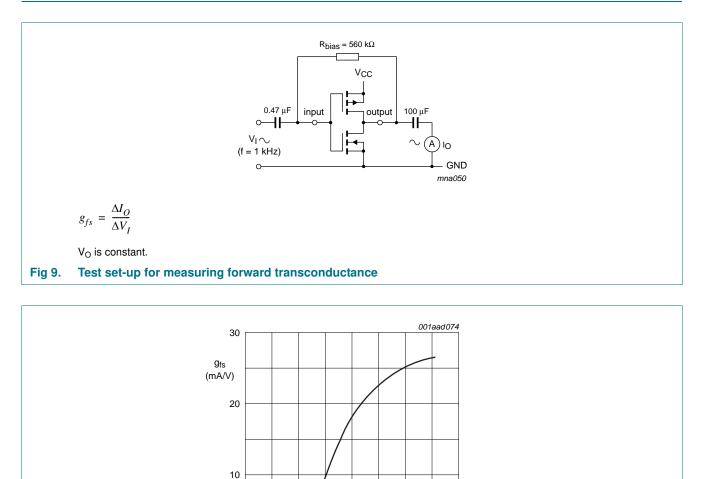
Supply voltage	Load		V <sub>EXT</sub>		
V <sub>cc</sub>	CL	RL <sup>[1]</sup>	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k $\Omega$ or 1 M $\Omega$	open	GND	$2 \times V_{CC}$

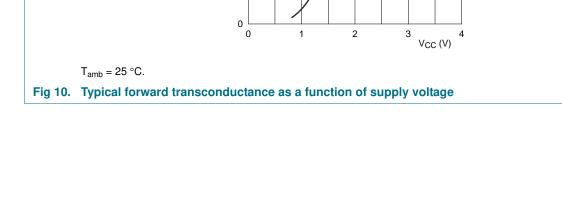
[1] For measuring enable and disable times  $R_L = 5 \text{ k}\Omega$ , for measuring propagation delays, set-up and hold times and pulse width  $R_L = 1 \text{ M}\Omega$ .

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## **13. Additional characteristics**



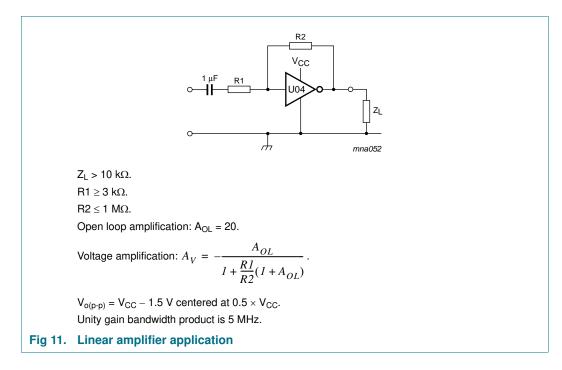


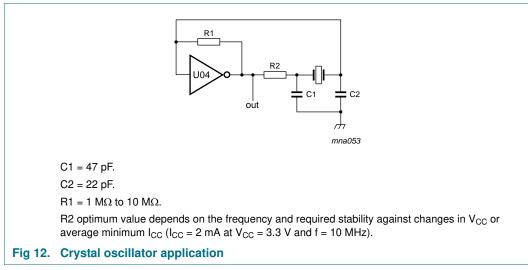
### 14. Application information

Some applications for the 74AUP2GU04 are:

- Linear amplifier (see Figure 11)
- Crystal oscillator (see Figure 12)

Remark: All values given are typical values unless otherwise specified.





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## 15. Package outline

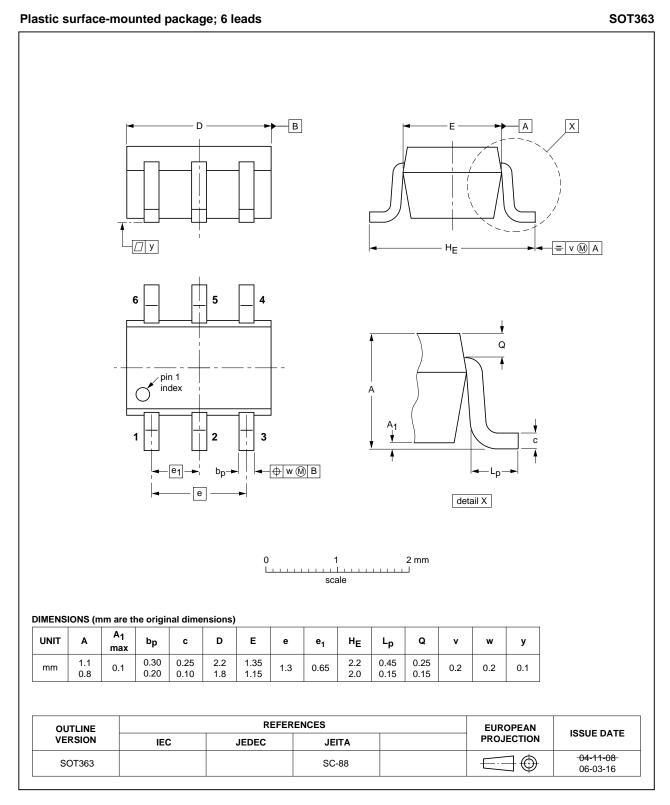
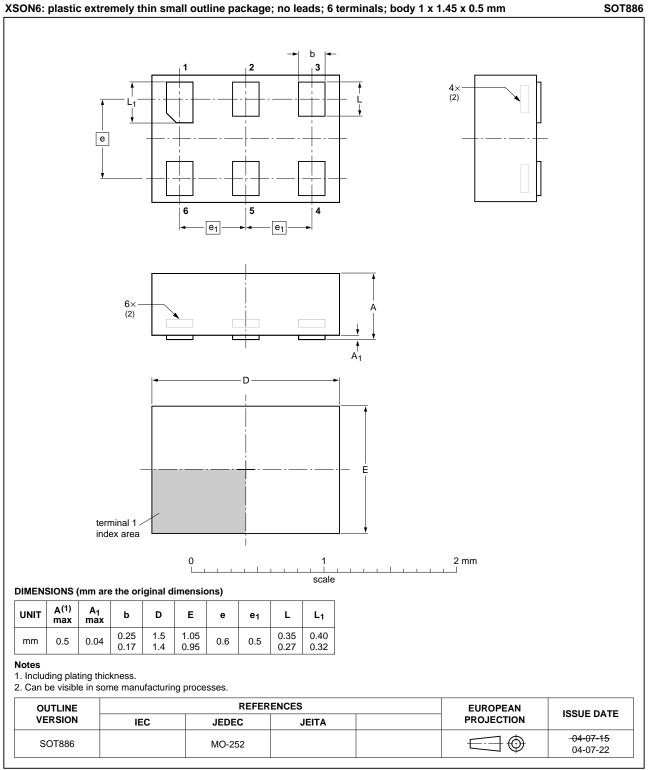


Fig 13. Package outline SOT363 (SC-88)

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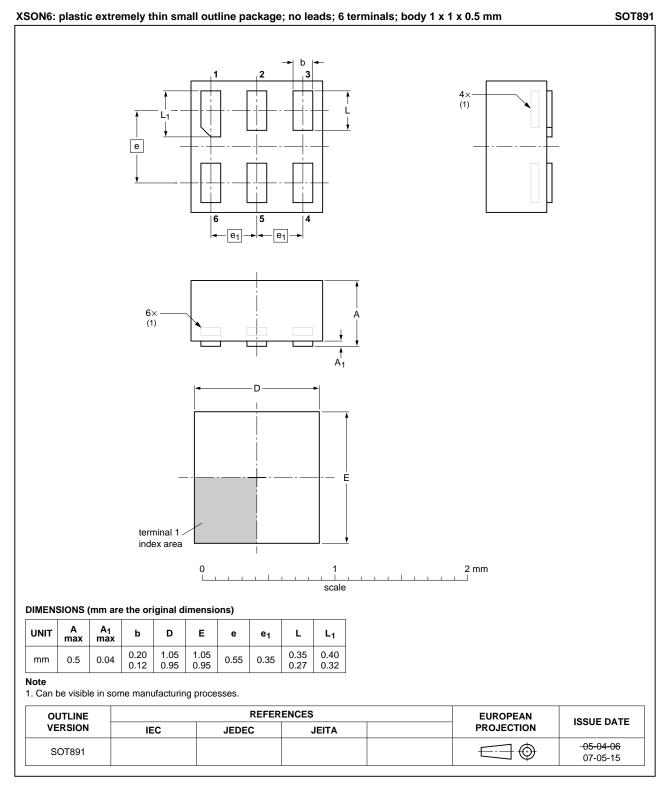


XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

#### Fig 14. Package outline SOT886 (XSON6)

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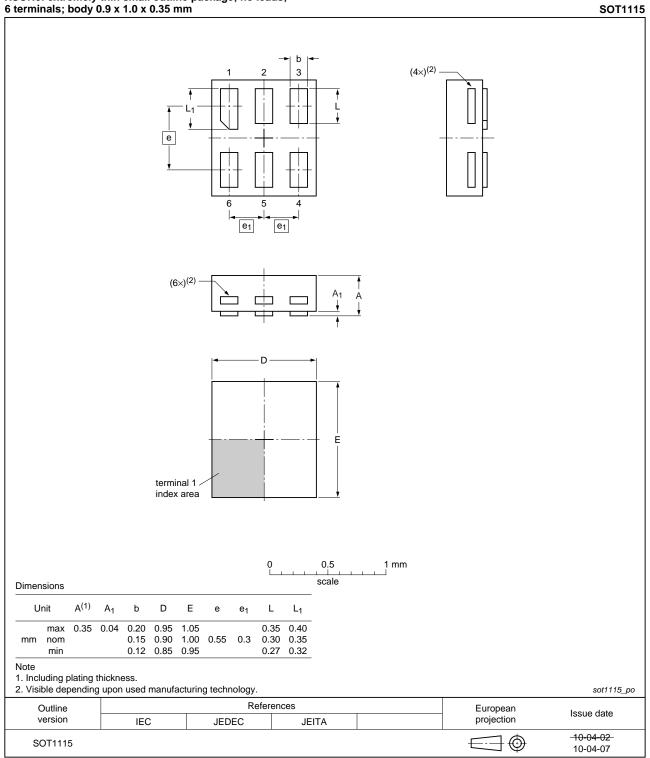
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#### Fig 15. Package outline SOT891 (XSON6)

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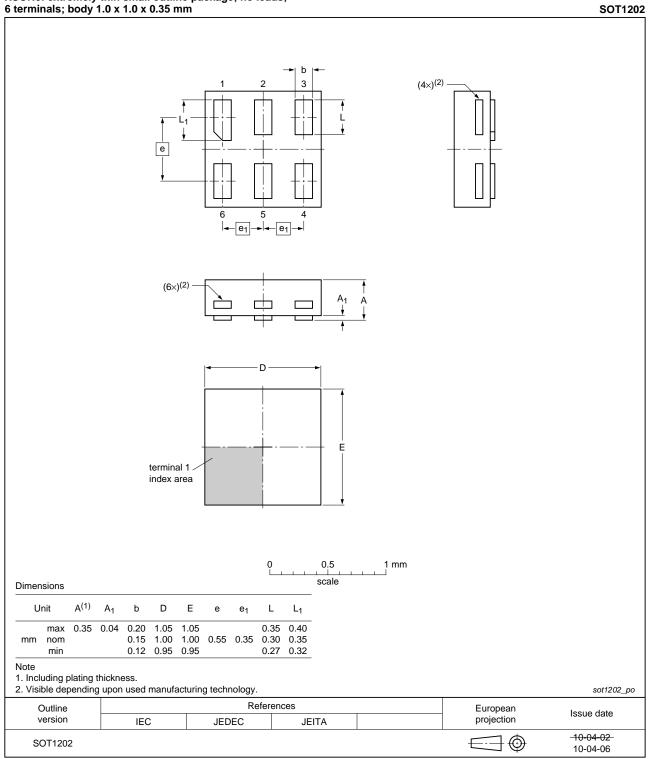


XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 16. Package outline SOT1115 (XSON6)

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XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 17. Package outline SOT1202 (XSON6)

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## 16. Abbreviations

Table 11. Abbreviations			
Description			
Charged Device Model			
Device Under Test			
ElectroStatic Discharge			
Human Body Model			
Machine Model			

## **17. Revision history**

### Table 12.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2GU04 v.4	20111207	Product data sheet	-	74AUP2GU04 v.3
Modifications:	<ul> <li>Legal pages</li> </ul>	updated.		
74AUP2GU04 v.3	20101110	Product data sheet	-	74AUP2GU04 v.2
74AUP2GU04 v.2	20090703	Product data sheet	-	74AUP2GU04 v.1
74AUP2GU04 v.1	20061215	Product data sheet	-	-

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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